



Description

JMT N-channel Enhancement Mode Power MOSFET

Features

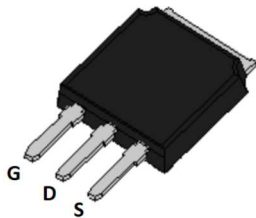
- 60V, 20A
 $R_{DS(ON)} < 29m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 40m\Omega @ V_{GS} = 4.5V$
- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

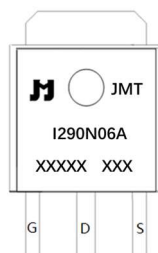
- Load Switch
- PWM Application
- Power management



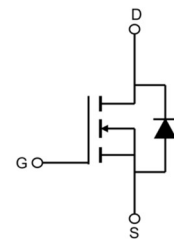
100% UIS TESTED!
100% ΔVds TESTED!



TO-251-4R top view



Marking and pin Assignment



Schematic Diagram

Device Marking	Device	OUTLINE	Device Package	TUBE (PCS)	Inner Box (PCS)	Per Carton (PCS)
JMTI290N06A	JMTI290N06A	TUBE	TO-251-4R	75	4,950	29,700

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	20
		$T_C = 100^\circ C$	13
I_{DM}	Pulsed Drain Current ^{note1}	80	A
EAS	Single Pulsed Avalanche Energy ^{note2}	20	mJ
P_D	Power Dissipation	$T_C = 25^\circ C$	22
$R_{\theta JC}$	Thermal Resistance, Junction to Case	6.8	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ C$



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.6	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} =10V, I _D =20A	-	21	29	mΩ
		V _{GS} =4.5V, I _D =15A	-	28	40	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	1562	-	pF
C _{oss}	Output Capacitance		-	75.4	-	pF
C _{rss}	Reverse Transfer Capacitance		-	66.8	-	pF
Q _g	Total Gate Charge	V _{DS} =30V, I _D =10A, V _{GS} =10V	-	25	-	nC
Q _{gs}	Gate-Source Charge		-	4.5	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	6.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =30V, I _D =20A, R _G =1.8Ω, V _{GS} =10V	-	7.5	-	ns
t _r	Turn-on Rise Time		-	21	-	ns
t _{d(off)}	Turn-off Delay Time		-	16	-	ns
t _f	Turn-off Fall Time		-	23.5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	20	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	80	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =20A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I _F =20A, di/dt=100A/μs	-	29	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	45	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25°C, V_{DD}=30V, V_G=10V, L=0.5mH, R_G=25Ω, I_{AS}=9A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure 1: Output Characteristics

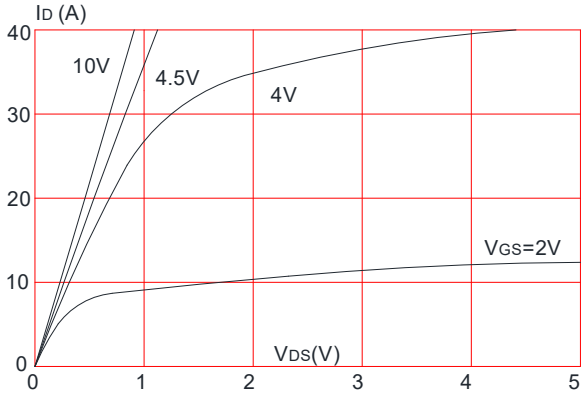


Figure 2: Typical Transfer Characteristics

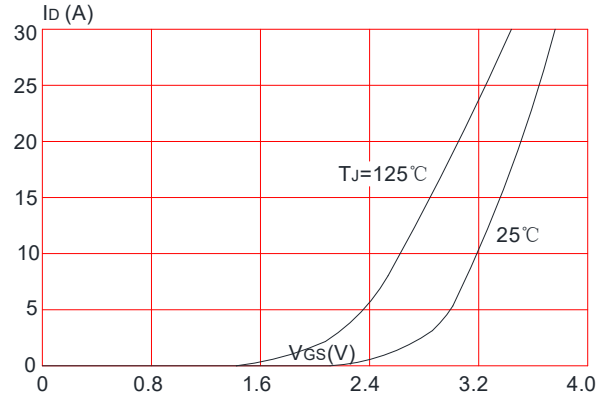


Figure 3: On-resistance vs. Drain Current

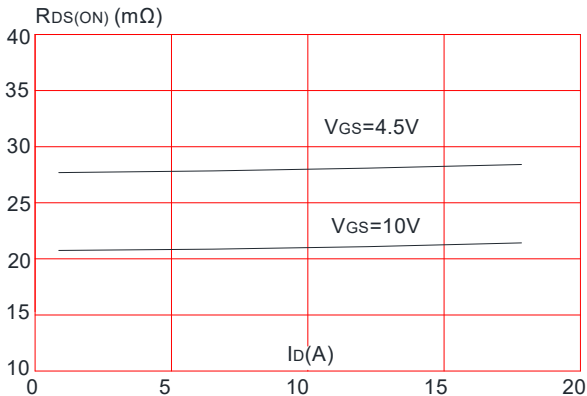


Figure 4: Body Diode Characteristics

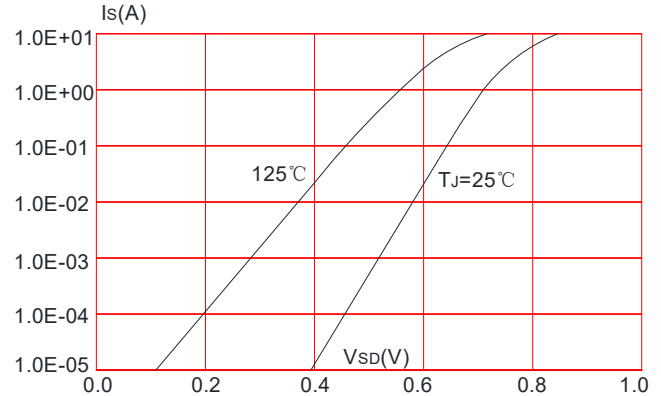


Figure 5: Gate Charge Characteristics

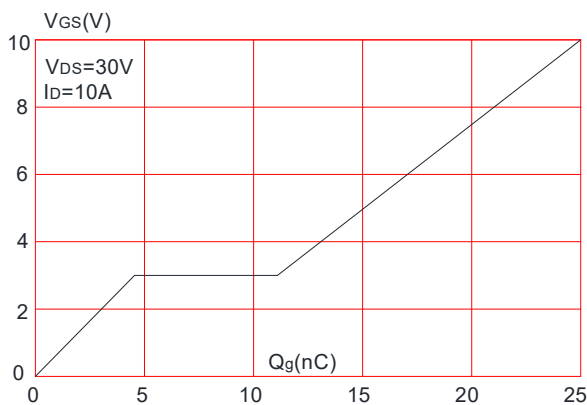


Figure 6: Capacitance Characteristics

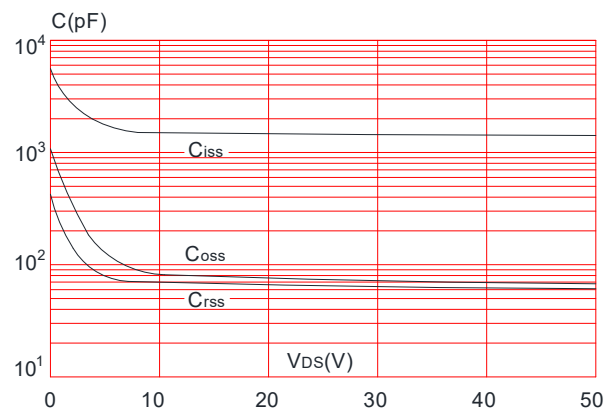




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

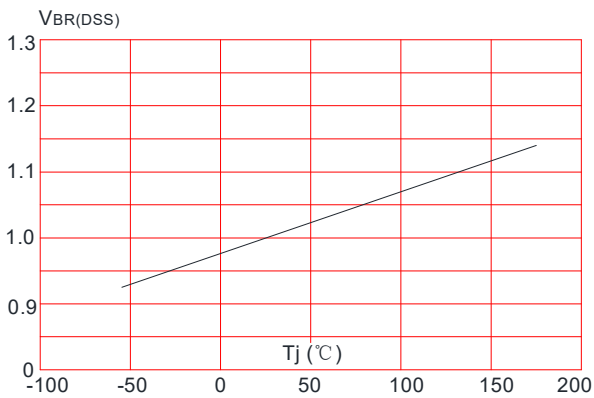


Figure 8: Normalized on Resistance vs. Junction Temperature

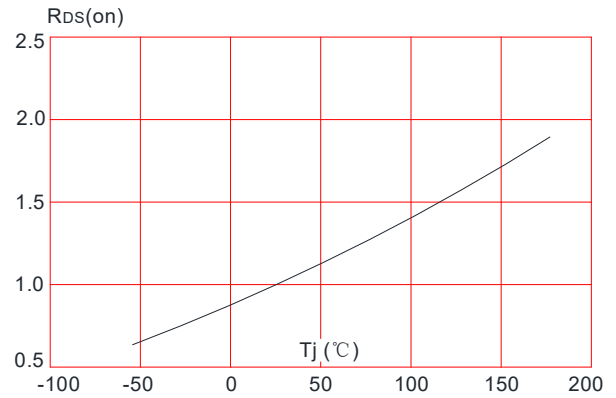


Figure 9: Maximum Safe Operating Area

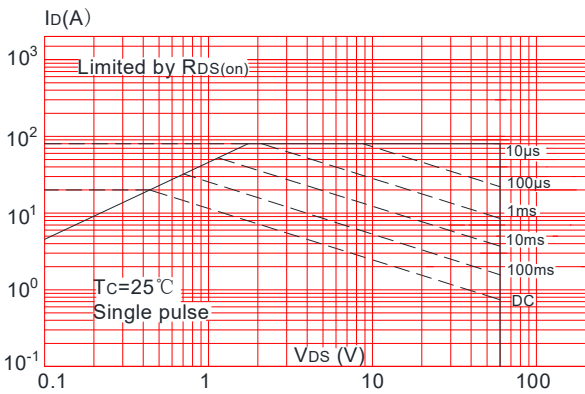


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

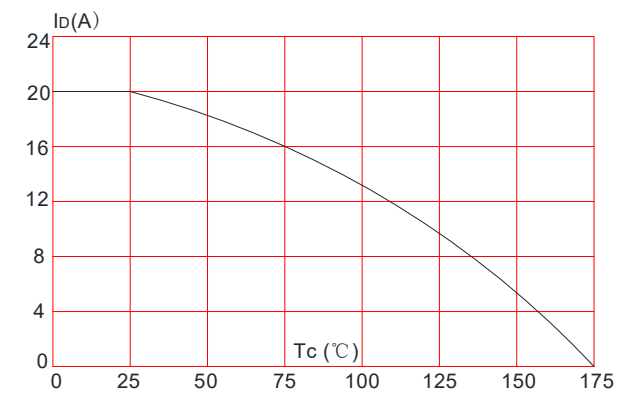
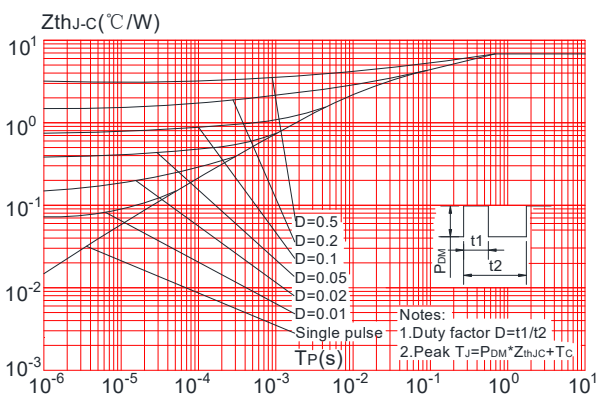


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform

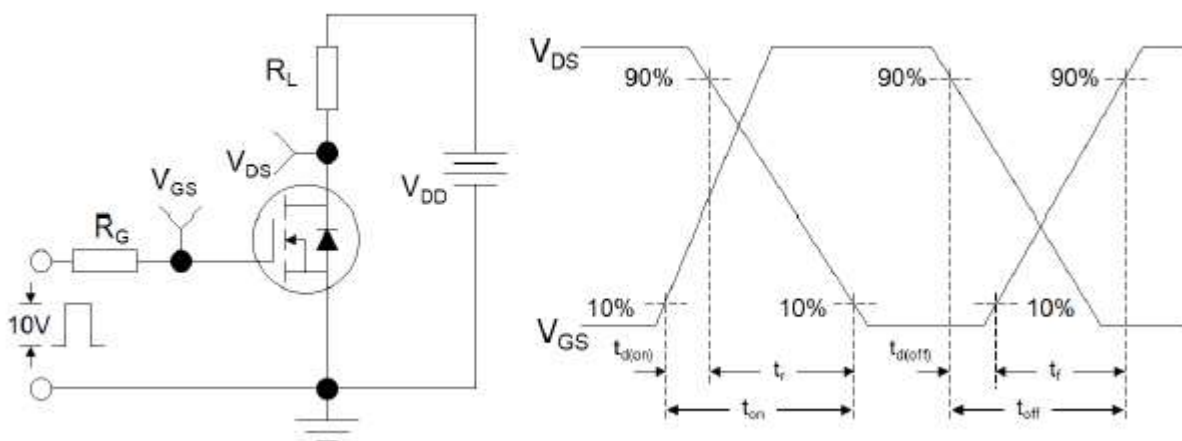


Figure 2: Resistive Switching Test Circuit & Waveforms

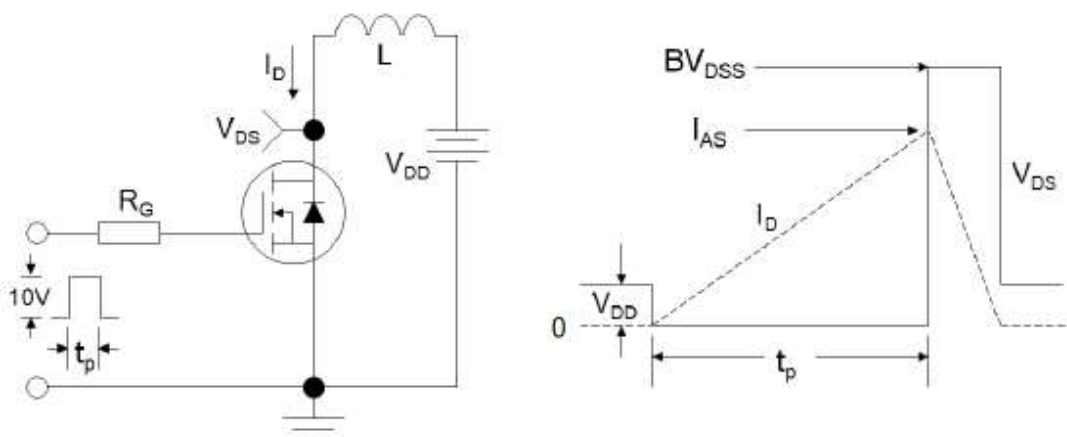
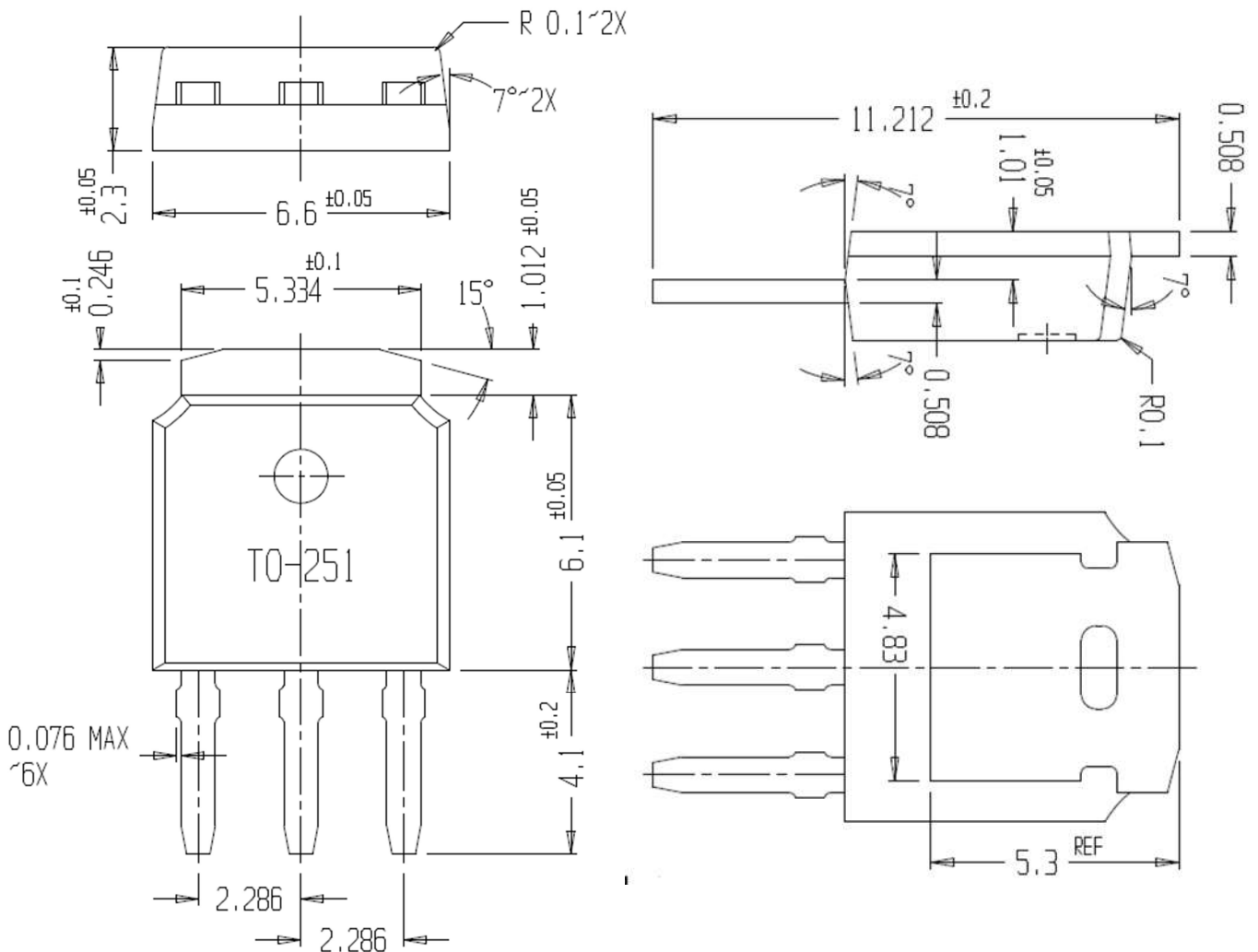


Figure 3: Unclamped Inductive Switching Test Circuit & Waveforms



Package Mechanical Data-TO-251-4R



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